

Silicon PNP Power Transistors

2SB1400

DESCRIPTION

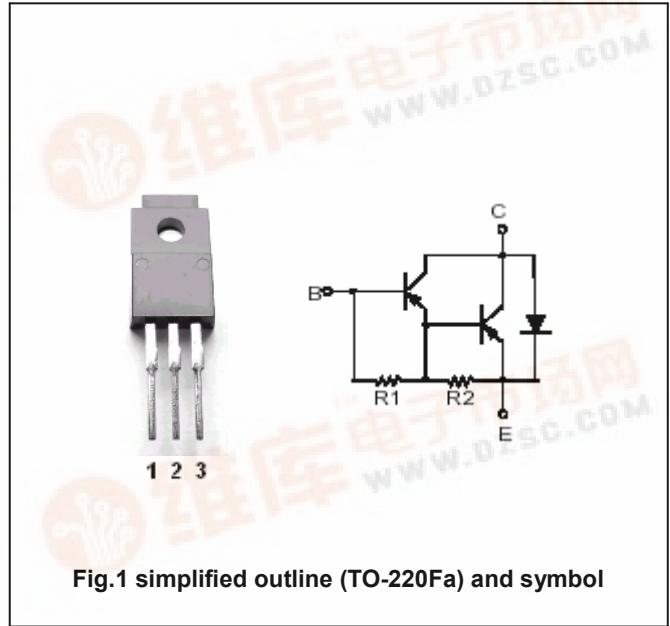
- With TO-220Fa package
- High DC current gain
- Low collector saturation voltage
- DARLINGTON

APPLICATIONS

- For use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector -emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-6	A
I _{CM}	Collector current-peak		-10	A
P _C	Collector power dissipation	T _a =25°C	2	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA; R _{BE} =∞	-120			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-100μA; I _E =0	-120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50mA; I _C =0	-7			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-3A ; I _B =-6mA			-1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-6A ; I _B =-60mA			-3.0	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =-3A ; I _B =-6mA			-2.0	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =-6A ; I _B =-60mA			-3.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{CEO}	Collector cut-off current	V _{CE} =-100V; R _{BE} =∞			-10	μA
h _{FE}	DC current gain	I _C =-3A ; V _{CE} =-3V	1000		20000	

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PACKAGE OUTLINE

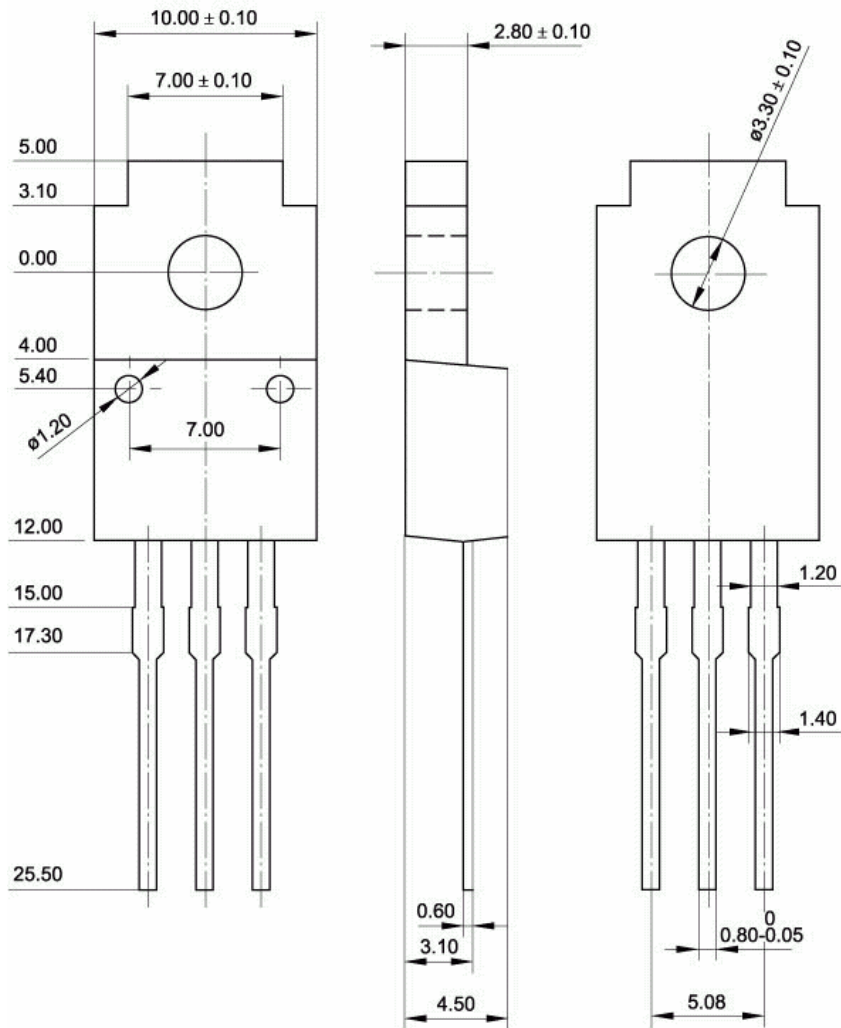


Fig.2 Outline dimensions (unindicated tolerance: ±0.15 mm)